

## ABSTRACT

[Problems] To provide a semiconductor device  
5 including a MIS-type FET having an excellent characteristic  
of low leakage current despite use of a high-K material of a  
high dielectric constant in a gate insulating film.

[Means for solving Problems] A MIS-type field-effect-  
transistor (FET) including: a silicon substrate (1); an  
10 insulating film (6) formed on the silicon substrate and  
containing silicon and at least one of nitrogen and oxygen; a  
metal oxide film formed on the insulating film and containing  
silicon and hafnium; and a gate electrode formed on the metal  
oxide film, wherein a silicon molar ratio ( $\text{Si}/(\text{Si}+\text{Hf})$ ) in the  
15 meal oxide film is in the range of 2 to 15%.